





#### **Description**

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G125 is a dual 3-State Buffer. Each buffer has an individual output enable pin while asserted HIGH will place the output in a high impedance state. The device is designed for operation over a power supply range of 0.8 V to 3.6 V. The device is fully specified for partial power down applications using  $I_{\rm OFF}$ . The  $I_{\rm OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

### **Pin Assignments**

(Top View)



X2-DFN1210-8

#### **Features**

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8 V to 3.6 V
- ± 4 mA Output Drive at 3.0 V
- Low Static Power Consumption
- Icc < 0.9 uA</li>
- Low Dynamic Power Consumption
- C<sub>PD</sub> = 6 pF Typical at 3.6 V
- Schmitt trigger action at all inputs make the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250 mV at Vcc = 3.0V
- I<sub>OFF</sub> Supports Partial-Power-Down Mode Operation
- ESD Protection per JESD 22

Exceeds 200-V Machine Model (A115)

Exceeds 2000-V Human Body Model (A114)

Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages per JESD30E
- DFN1210 Denoted as X2-DFN1210-8
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Applications**

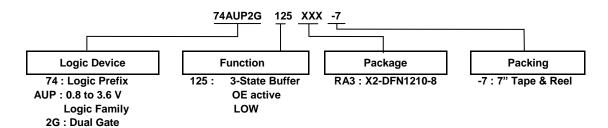
- Suited for Battery and Low Power Needs
- Wide array of products such as:
  - Tablets, E-readers
  - Cell Phones, Personal Navigation / GPS
  - MP3 Players, Cameras, Video Recorders
  - PCs, Ultrabooks, Notebooks, Netbooks
  - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
  - TV, DVD, DVR, Set-Top Box

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



### **Ordering Information**



Device	Package	Package	Package	7" Tape and Reel			
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix		
74AUP2G125RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0 mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7		

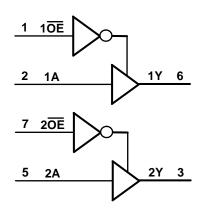
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf

### **Pin Descriptions**

Pin Name	Pin NO.	Description
1 <b>OE</b>	1	Output Enable active LOW
1A	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
1Y	6	Data Output
2 <b>OE</b>	7	Output Enable active LOW
V <sub>CC</sub>	8	Supply Voltage

# **Logic Diagram**



## **Function Table**

Inp	uts	Output
ŌĒ	Α	Y
L	Н	Н
L	L	L
Н	Х	Z



# Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
Vcc	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V <sub>CC</sub> +0.5	V
lıĸ	Input Clamp Current V <sub>I</sub> < 0	50	mA
lok	Output Clamp Current (V <sub>O</sub> < 0 )	50	mA
Io	Continuous Output Current (V <sub>O</sub> = 0 to V <sub>CC</sub> )	±20	mA
Icc	Continuous Current Through V <sub>CC</sub>	50	mA
I <sub>GND</sub>	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Notes:

# **Recommended Operating Conditions** (Note 8)

Symbol	Param	eter	Min	Max	Unit
V <sub>CC</sub>	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	Vcc	V
		V <sub>CC</sub> = 0.8V	_	-20	μA
	I <sub>OH</sub> High-Level Output Current	V <sub>CC</sub> = 1.1V	_	-1.1	
		$V_{CC} = 1.4V$	_	-1.7	
ЮН		V <sub>CC</sub> = 1.65V	_	-1.9	mA
		$V_{CC} = 2.3V$	_	-3.1	
		$V_{CC} = 3.0V$	_	-4	
		$V_{CC} = 0.8V$	_	20	μΑ
		V <sub>CC</sub> = 1.1V	_	1.1	
	Lave Lavel Output Company	V <sub>CC</sub> = 1.4V	_	1.7	
l <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 1.65V	_	1.9	mA
		V <sub>CC</sub> = 2.3V	_	3.1	
		V <sub>CC</sub> = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate V <sub>CC</sub> = 0.8V to 3.6V		_	200	ns/V
TA	Operating Free-Air Temperature		-40	125	°C

Note: 8. Unused inputs should be held at  $V_{CC}$  or Ground.

<sup>6.</sup> Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

<sup>7.</sup> Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



### **Electrical Characteristics**

Cumala al	Donomenten	Took Complision -	V	T <sub>A</sub> = +	-25°C	T <sub>A</sub> = -40°C	I I mile		
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	Min	Max	Min	Max	Unit	
		_	0.8V to 1.65V	0.80 X V <sub>CC</sub>	_	0.80 X V <sub>CC</sub>	_		
\ /	High-Level Input	_	1.65V to 1.95V	0.65 X V <sub>CC</sub>	_	0.65 X V <sub>CC</sub>	_	.,	
$V_{IH}$	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	V	
		_	3.0V to 3.6V	2.0	_	2.0	_		
		_	0.8V to 1.65V	_	0.30 X V <sub>CC</sub>	_	0.30 X V <sub>CC</sub>		
V	Low-Level Input	_	1.65V to 1.95V	_	0.35 X V <sub>CC</sub>	_	0.35 X V <sub>CC</sub>	V	
$V_{IL}$	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	7 °	
		_	3.0V to 3.6V	_	0.9	_	0.9		
		I <sub>OH</sub> = -20μA 0.8\		V <sub>CC</sub> – 0.1	_	V <sub>CC</sub> – 0.1	_		
		$I_{OH} = -1.1 \text{mA}$	1.1V	0.75 X V <sub>CC</sub>	_	0.7 X V <sub>CC</sub>	_		
		I <sub>OH</sub> = -1.7mA	1.4V	1.11	_	1.03	_		
	High-Level Output	I <sub>OH</sub> = -1.9mA	1.65V	1.32	_	1.3	_	.,	
VoH	Voltage	I <sub>OH</sub> = -2.3mA	0.01/	2.05	_	1.97	_	V	
		I <sub>OH</sub> = -3.1mA	2.3V	1.9	_	1.85	_		
		I <sub>OH</sub> = -2.7mA		2.72	_	2.67	_		
		I <sub>OH</sub> = -4mA	3V	2.6	_	2.55	_		
		I <sub>OL</sub> = 20μA	0.8V to 3.6V	_	0.1	_	0.1		
		I <sub>OL</sub> = 1.1mA	1.1V	_	0.3 X V <sub>CC</sub>	_	0.3 X V <sub>CC</sub>		
		I <sub>OL</sub> = 1.7mA	1.4V	_	0.31	_	0.37		
	Low-Level Output	I <sub>OL</sub> = 1.9mA	1.65V	_	0.31	_	0.35		
$V_{OL}$	Voltage	I <sub>OL</sub> = 2.3mA		_	0.31	_	0.33	V	
		I <sub>OL</sub> = 3.1mA	2.3V	_	0.44	_	0.45		
		I <sub>OL</sub> = 2.7mA		_	0.31	_	0.33	1	
		I <sub>OL</sub> = 4mA	3V	_	0.44	_	0.45	1	
lį	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0 to 3.6V	_	± 0.1	_	± 0.5	μΑ	
l <sub>OZ</sub>	Z-State Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0 to 3.6V	_	0.2	_	± 0.5	μΑ	
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 =$ 0V to 3.6V	0 V		± 0.2		± 0.5	μA	
$\Delta I_{OFF}$	Delta Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0 V to 0.2V	_	0.2	_	0.6	μA	
I <sub>CC</sub>	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O$ = 0	0.8 V to 3.6V	_	0.5	_	0.9	μΑ	
		Data Input at V <sub>CC</sub> -0.6 V OE= GND I <sub>O</sub> =0 A	3.3V	_	40	_	50	μA	
$\Delta I_{CC}$	ΔI <sub>CC</sub> Additional Supply	OE Input at VCC -0.6 V Data Input= GND or Vcc I <sub>O</sub> =0 A	3.3V	_	110	_	120	μA	
		OE Input at VCC Data Input= GND to 3.6 V I <sub>O</sub> =0 A	0.8V to 3.6V	_	1	_	1	μA	



# **Electrical Characteristics** (cont.)

Cumala al	Dawawatan	Took Conditions	v	T <sub>A</sub> = -40°C to	+125°C	l lm it	
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	Min	Max	Unit	
		_	0.8V to 1.65V	0.80 X V <sub>CC</sub>	_		
	High-Level Input	_	1.65V to 1.95V	0.70 X V <sub>CC</sub>	_	V	
$V_{IH}$	Voltage	_	2.3V to 2.7V	1.6	_	7 V	
		_	3.0V to 3.6V	2.0	_		
		_	0.8V to 1.65V	_	0.25 X V <sub>CC</sub>		
$V_{IL}$	Low-Level Input	_	1.65V to 1.95V	_	0.30 X V <sub>CC</sub>	V	
۷IL	Voltage	_	2.3V to 2.7V	_	0.7	_ v	
		_	3.0V to 3.6V	_	0.9		
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V <sub>CC</sub> – 0.11	_		
		$I_{OH} = -1.1 \text{mA}$	1.1V	0.6 X V <sub>CC</sub>	_		
	High-Level Output	$I_{OH} = -1.7 \text{mA}$	1.4V	0.93	_		
.,		$I_{OH} = -1.9 \text{mA}$	1.65V	1.17	_	V	
V <sub>OH</sub>	Voltage	I <sub>OH</sub> = -2.3mA	2.21/	1.77	_	\ \	
		I <sub>OH</sub> = -3.1mA	2.3V	1.67	_		
		I <sub>OH</sub> = -2.7mA	3V	2.40	_		
		I <sub>OH</sub> = -4mA		2.30	_		
		I <sub>OL</sub> = 20μA	0.8V to 3.6V	_	0.11		
		I <sub>OL</sub> = 1.1mA	1.1V	_	0.33 X V <sub>CC</sub>		
		$I_{OL} = 1.7 \text{mA}$	1.4V	_	0.41	1	
	Low-Level Output	I <sub>OL</sub> = 1.9mA	1.65V	_	0.39	Ī	
$V_{OL}$	Voltage	I <sub>OL</sub> = 2.3mA		_	0.36	V	
		I <sub>OL</sub> = 3.1mA	2.3V	_	0.50		
		$I_{OL} = 2.7 \text{mA}$		_	0.36	1	
		I <sub>OL</sub> = 4mA	3V	_	0.50		
I <sub>I</sub>	Input Current	A or B Input, V <sub>I</sub> = GND to 3.6V	0 to 3.6V	_	± 0.75	μA	
l <sub>OZ</sub>	Z-State Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0 to 3.6V	_	± 1.5	μΑ	
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0	_	± 3.5	μA	
$\Delta I_{OFF}$	Delta Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μΑ	
		Data Input at $V_{CC}$ =0.6 V OE= GND I <sub>O</sub> =0 A	3.3V	_	75	μА	
Δl <sub>cc</sub>	Additional Supply  Current	OE Input at VCC -0.6 V Data Input= GND or Vcc I <sub>0</sub> =0 A	3.3V	_	180	μА	
		OE Input at VCC Data Input= GND to 3.6 V I <sub>o</sub> =0 A	0.8V to 3.6V	_	1	μА	



# Operating and Package Characteristics (@TA = +25°C, unless otherwise specified.)

	Parameter	Test Condition	s	Vcc	Тур	Unit
				0.8V	6.5	
				1.2V ± 0.1V	6.3	
0	C <sub>pd</sub> Power Dissipation Capacitance per gate	f = 1MHz Output Enab		1.5V ± 0.1V	6.3	,,
$C_{pd}$		No Load		1.8V ± 0.15V	6.2	pF
		140 2000		2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
Ci	Input Capacitance	$V_i = V_{CC}$ or G	SND	0V or 3.3V	1.5	pF
0	Output Canacitanas	Output Enabled \	√o=Gnd	0 V	2.9	pF
Co	Output Capacitance	Output Disabled VO=	Gnd or Vcc	0V or 3.6V	2.1	pF
θЈА	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8 (Note 9)		_	395	°C/W
$\theta_{JC}$	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	_	236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



# **Switching Characteristics**

 $C_L = 5pF$ , See Figure 1

					T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	
Parameter	From Input	To Output	V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	20.6	_	_	_	_	_	
		1.2V ± 0.1V	2.8	5.5	12.6	2.5	14.0	2.5	17	<b>_</b>	
	۸	Y	1.5V ± 0.1V	2.2	3.9	7.3	2.0	7.5	2.0	8.1	ns
t <sub>pd</sub>	Α	ĭ	1.8V ± 0.15V	1.9	3.2	4.8	1.7	6.1	1.7	6.7	
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9	
			3.3V ± 0.3V	1.4	2.4	3.1	1.2	3.9	1.2	4.4	
		Y	V8.0	_	69.9	_	_	_	_	_	ns
			1.2V ± 0.1V	3.1	6.1	14.2	2.9	20	2.9	22.2	
	<del></del>		1.5V ± 0.1V	2.5	4.2	7.9	2.3	9.2	2.3	10.0	
t <sub>en</sub>	ŌĒ		1.8V ± 0.15V	2.1	3.4	6.1	2.0	7.4	2.0	8.2	
			2.5V ± 0.2V	1.8	2.6	4.4	1.7	5.4	1.7	6.0	
			$3.3V \pm 0.3V$	1.7	2.4	4.0	1.7	4.6	1.7	5.1	
			V8.0	_	14.3	_	_	_	_	_	
			1.2V ± 0.1V	2.7	4.3	9.4	2.7	10.6	2.7	11.8	
	<del></del>	Y	1.5V ± 0.1V	2.1	3.2	6.4	2.1	7.3	2.1	8.2	
t <sub>dis</sub>	ŌĒ	ľ	1.8V ± 0.15V	2.0	3.0	5.5	2.0	6.3	2.0	7.1	ns -
			2.5V ± 0.2V	1.4	2.2	3.7	1.4	4.2	1.4	5.1	
			3.3V ± 0.3V	1.7	2.5	4.4	1.7	4.6	1.7	5.4	

C<sub>L</sub> = 10pF, See Figure 1

Parameter	From	То	V		T <sub>A</sub> = +25°C	;	T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit
Farameter	Input	Output	V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Oiii
			V8.0	_	24.0	_	_	_	_	-	
			1.2V ± 0.1V	3.2	6.4	14.8	3.0	16.6	3.0	18.2	
, ,	Y	1.5V ± 0.1V	2.1	4.5	8.8	1.9	9.1	1.9	9.4		
<b>l</b> pd	t <sub>pd</sub> A	ı	1.8V ± 0.15V	1.9	3.8	5.5	1.7	6.8	1.7	7.6	ns
			2.5V ± 0.2V	2.1	3.2	4.2	1.6	5.3	1.6	5.9	
			$3.3V \pm 0.3V$	1.8	3.0	3.8	1.6	4.6	1.6	5.2	
		V8.0	_	73.7	_	_	_	_	l		
		Y	1.2V ± 0.1V	3.6	6.9	16.2	3.4	22.8	3.4	25.2	ns
	ŌĒ		1.5V ± 0.1V	2.3	4.8	9.2	2.2	10.3	2.2	11.3	
t <sub>en</sub>	OE		1.8V ± 0.15V	2.0	3.9	7.0	1.9	8.2	1.9	8.9	
			2.5V ± 0.2V	1.8	3.2	5.2	1.7	6.4	1.7	7.1	
			3.3V ± 0.3V	1.7	3.0	5.1	1.7	5.6	1.7	6.2	
			V8.0	_	32.7	_	_	_	_	_	
			1.2V ± 0.1V	3.4	5.4	11.4	3.4	12.7	3.4	14.3	
	ŌĒ	Y	1.5V ± 0.1V	2.2	4.1	7.9	2.2	8.9	2.2	10.2	
t <sub>dis</sub>	UE	r	1.8V ± 0.15V	2.2	4.2	7.0	1.9	8.0	1.9	8.9	ns
			2.5V ± 0.2V	1.7	3.0	4.8	1.7	5.7	1.7	6.4	1
			$3.3V \pm 0.3V$	2.1	3.8	6.5	1.7	6.8	1.7	7.7	



## **Switching Characteristics** (cont.)

 $C_L = 15pF$ , See Figure 1

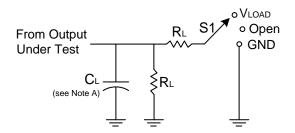
Parameter	From	То	V		T <sub>A</sub> = +25°C	;	T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit
rarameter	Input	Output	Vcc	Min	Тур	Max	Min	Max	Min	Max	Ollit
			V8.0	_	27.4	_	_	_	_	_	
			1.2V ± 0.1V	3.6	7.2	15.8	3.3	22.4	3.3	22.5	
t <sub>pd</sub> A	Y	1.5V ± 0.1V	3.0	5.1	8.8	2.5	9.8	2.5	10.9	ns	
	ı	1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8		
			2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7	
			$3.3V \pm 0.3V$	2.0	3.5	4.4	1.8	5.4	1.8	6.1	1
		Y	0.8V	_	77.5	_	_	_	_	_	
			1.2V ± 0.1V	4.0	7.7	18.2	3.7	21.8	3.7	23.5	ns
	ŌĒ		1.5V ± 0.1V	3.0	5.3	10.1	2.5	11.8	2.5	12.8	
t <sub>en</sub>	OE	ı	1.8V ± 0.15V	2.3	4.4	7.8	2.1	9.2	2.1	10.2	
			2.5V ± 0.2V	2.1	3.6	6.0	2.0	7.3	2.0	8.2	
			$3.3V \pm 0.3V$	2.0	3.5	5.7	1.9	6.4	1.9	7.2	
			0.8V	_	60.8	_	_	_	_	_	
			1.2V ± 0.1V	4.3	6.5	13.9	3.7	15.5	3.7	15.7	
	<del></del>	Y	1.5V ± 0.1V	3.0	5.0	8.8	2.5	9.7	2.5	9.8	
t <sub>dis</sub>	ŌĒ	ſ	1.8V ± 0.15V	3.0	5.3	8.8	2.1	10.3	2.1	10.5	ns
			2.5V ± 0.2V	2.1	3.8	8.2	2.0	8.4	2.0	8.6	1
			$3.3V \pm 0.3V$	2.9	5.0	8.6	1.9	9.2	1.9	9.4	

 $C_L = 30pF$ , See Figure 1

Parameter	From	То	V		T <sub>A</sub> = +25°C	;	T <sub>A</sub> = -40°0	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit
Faranietei	Input	Output	V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Ullit
			V8.0	_	37.4	_	_	_	_	_	
			1.2V ± 0.1V	4.8	9.5	21	4.4	24.9	4.4	25	
t <sub>pd</sub> A	Y	1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	]	
	ĭ	1.8V ± 0.15V	2.9	5.6	8.4	2.6	10.3	2.6	11.5	ns	
			2.5V ± 0.2V	2.7	4.8	6.3	2.5	7.8	2.5	8.7	
			3.3V ± 0.3V	2.7	4.6	6	2.5	7.5	2.5	8.3	1
		Y	V8.0	_	88.9	_	_	_	_	_	ns
			1.2V ± 0.1V	5.2	9.9	23.8	4.8	27.4	4.8	30.4	
	<del></del>		1.5V ± 0.1V	4.0	6.8	13.0	3.1	15.1	3.1	16.9	
t <sub>en</sub>	ŌĒ		1.8V ± 0.15V	3.0	5.6	10.2	2.8	12.2	2.8	13.6	
			2.5V ± 0.2V	2.7	4.8	7.8	2.6	9.4	2.6	10.6	
			3.3V ± 0.3V	2.7	4.6	7.8	2.6	9.0	2.6	10.0	
			V8.0	_	49.9	_	_	_	_	_	
			1.2V ± 0.1V	6.0	9.9	16.0	4.8	17.8	4.8	19.8	
	<u> </u>	Y	1.5V ± 0.1V	4.4	7.7	11.5	3.1	13.0	3.1	14.5	
t <sub>dis</sub>	ŌĒ	r	1.8V ± 0.15V	5.1	8.7	13.3	2.8	14.9	2.8	16.6	ns
		_	2.5V ± 0.2V	3.6	6.2	9.1	2.6	10.3	2.6	11.5	1
			3.3V ± 0.3V	5.2	8.7	13.7	2.6	14.0	2.6	17.0	



#### **Parameter Measurement Information**

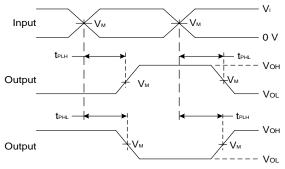


TEST	<b>S</b> 1	$R_{L}$
t <sub>PLH</sub> /t <sub>PHL</sub>	Open	1ΜΩ
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vload	5ΚΩ
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND	5ΚΩ

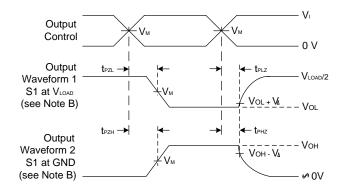
Voc	In	puts		V <sub>LOAD</sub>		<b>V</b> Δ
Vcc	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>		C <sub>L</sub>	
0.8V	Vcc	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1 V
1.2V±0.1V	Vcc	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1 V
1.5V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1 V
1.8V ±0.15V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.15 V
2.5V±0.2V	Vcc	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.15 V
3.3V±0.3V	Vcc	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.3V



**Voltage Waveform Pulse Duration** 



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times
Low and High Level Enabling

#### Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$
- E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{EN}$ .
- F. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD</sub>.



### **Marking Information**

#### X2-DFN1210-8

(Top View)

XX: Identification Code

Y : Year : 0~9

 $\underline{W}$ : week: A~Z: 1~26 week

a~z: 27-52 week

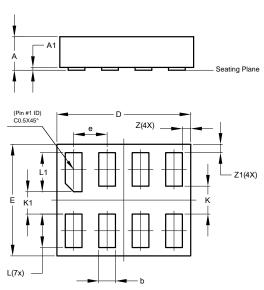
z represents 52 and 53 week

 $\underline{X}$ : week: A~Z: Internal code

Part Number	Package	Identification Code	
74AUP2G125RA3-7	X2-DFN1210-8	JT	

# X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



		-	x	1	-	
Y1	↓ ▼ G —					_
<u> </u>	Ĭ _					<b>A</b>
	_	_ c	_		_ x _	—

X2-DFN1210-8				
Dim	Min	Max	Тур	
Α	-	0.35	0.30	
A1	0	0.03	0.02	
b	0.10	0.20	0.15	
D	1.15	1.25	1.20	
E	0.95	1.05	1.00	
е	-	-	0.30	
K	-	-	0.25	
K1	-	-	0.20	
L	0.25	0.35	0.30	
L1	0.30	0.40	0.35	
Z	0.050	0.100	0.075	
<b>Z</b> 1	0.050	0.100	0.075	
All Dimensions in mm				

Dimensions	Value (in mm)
С	0.300
G	0.150
Х	0.150
X1	1.050
Υ	0.500
Y1	1.150

January 2015

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